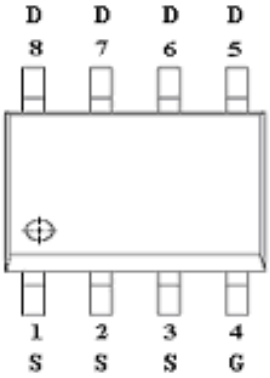
SPP9433W
P-Channel Enhancement Mode MOSFET

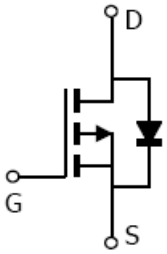
DESCRIPTION
The SPP9433W is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.
This high density process is especially tailored to minimize on-state resistance.
These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

FEATURES
- -30V/-6A,$R_{DS(ON)}$=42mΩ@V_{GS}=-10V
- -30V/-3A,$R_{DS(ON)}$=78mΩ@V_{GS}=-4.5V
- Super high density cell design for extremely low $R_{DS\ (ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP-8 package design

APPLICATIONS
- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- LCD Display inverter

PIN CONFIGURATION(SOP–8)





PART MARKING

A : Lot Code
B : Date Code

SPP9433W
P-Channel Enhancement Mode MOSFET

PIN DESCRIPTION

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

ORDERING INFORMATION

Part Number	Package	Part Marking
SPP9433WS8RGB	SOP-8	SPP9433W

※ SPP9433WS8RGB : 13" Tape Reel ; Pb – Free ; Halogen - Free

ABSOULTE MAXIMUM RATINGS

(T_A=25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-30	V
Gate –Source Voltage		V_{GSS}	±20	V
Continuous Drain Current(T_J=150℃)	T_A=25℃	I_D	-6	A
	T_A=70℃		-4	
Pulsed Drain Current		I_{DM}	-12	A
Continuous Source Current(Diode Conduction)		I_S	-6	A
Power Dissipation	T_A=25℃	P_D	2.08	W
Operating Junction Temperature		T_J	-55/150	℃
Storage Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	60	℃/W

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ELECTRICAL CHARACTERISTICS

(T_A=25℃ Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250uA	-1.0		-2.5	
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V,V_{GS}=0V			-1	uA
		V_{DS}=-24V,V_{GS}=0V T_J=55℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦-5V,V_{GS}=-10V	-6			A
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=- 10V,I_D=-6A		0.035	0.042	Ω
		V_{GS}=- 4.5V,I_D=-3A		0.065	0.078	
Forward Transconductance	gfs	V_{DS}=-10.0V,I_D=-6A		6		S
Diode Forward Voltage	V_{SD}	I_S=-6A,V_{GS}=0V			-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-20V, V_{GS}=-4.5V I_D=-6A		6.4		nC
Gate-Source Charge	Q_{gs}			2.7		
Gate-Drain Charge	Q_{gd}			3.1		
Input Capacitance	C_{iss}	V_{DS}=-24V,V_{GS}=0V f=1MHz		650		pF
Output Capacitance	C_{oss}			270		
Reverse Transfer Capacitance	C_{rss}			104		
Turn-On Time	$t_{d(on)}$	V_{DD}=-12V, I_D=-5.0A, V_{GEN}=-10V R_G=3.3Ω		9		nS
	t_r			16		
Turn-Off Time	$t_{d(off)}$			21		
	t_f			22		

TYPICAL CHARACTERISTICS

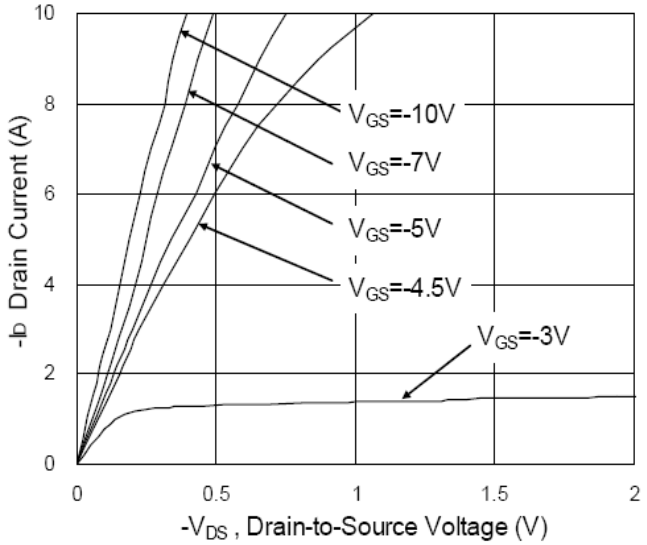

Fig. 1 Typical Output Characteristics

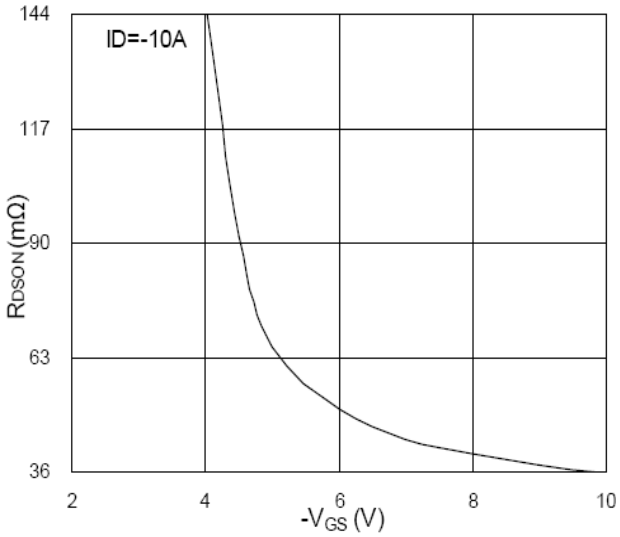

Fig. 2 On-Resistance vs. Gate Voltage

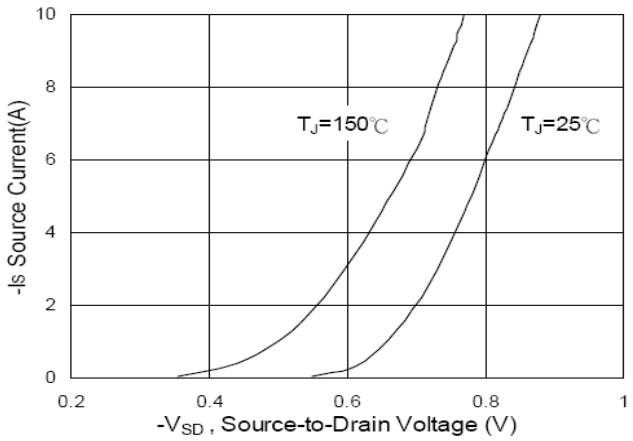

Fig. 3 Forward characteristics of Diodes

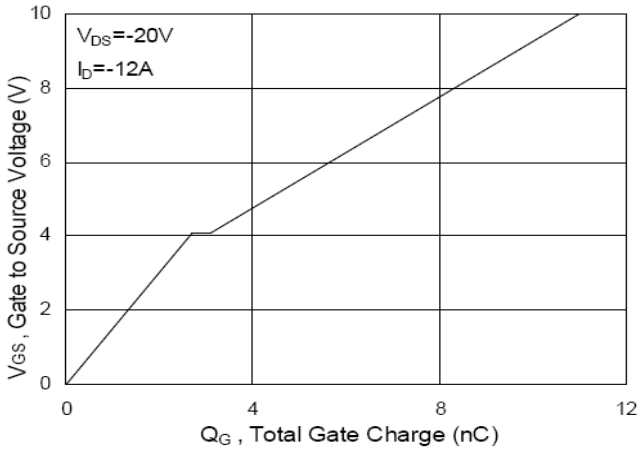

Fig. 4 Gate Charge Characteristics

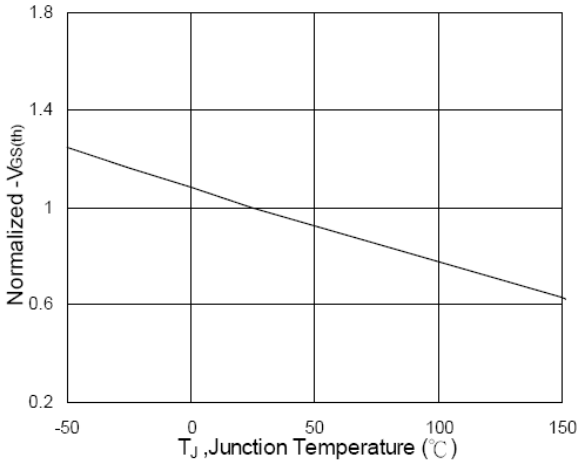

Fig. 5 Vgs vs. Junction Temperature

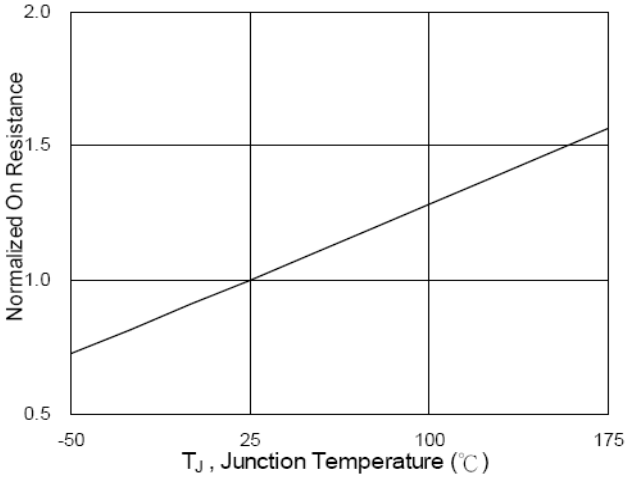

Fig. 6 On-Resistance vs Junction Temp

TYPICAL CHARACTERISTICS

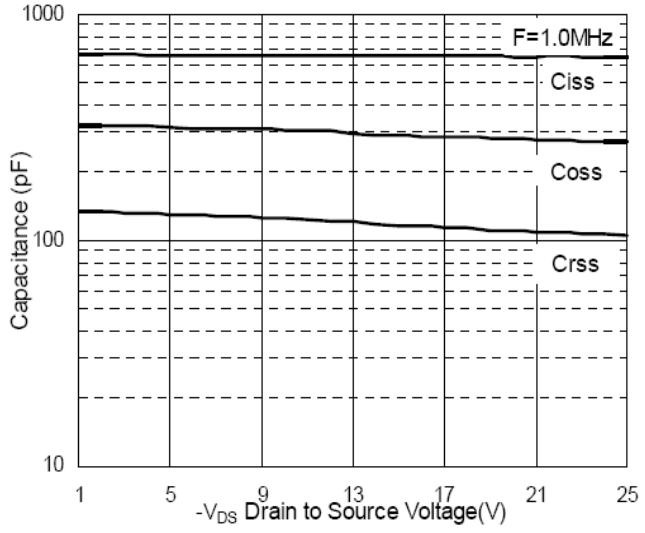

Fig. 7 Typical Capacitance Characteristics

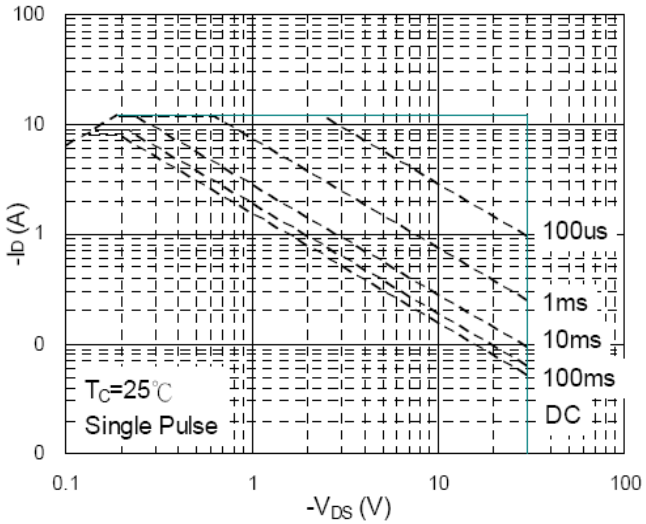

Fig. 8 Maximum Safe Operation Area

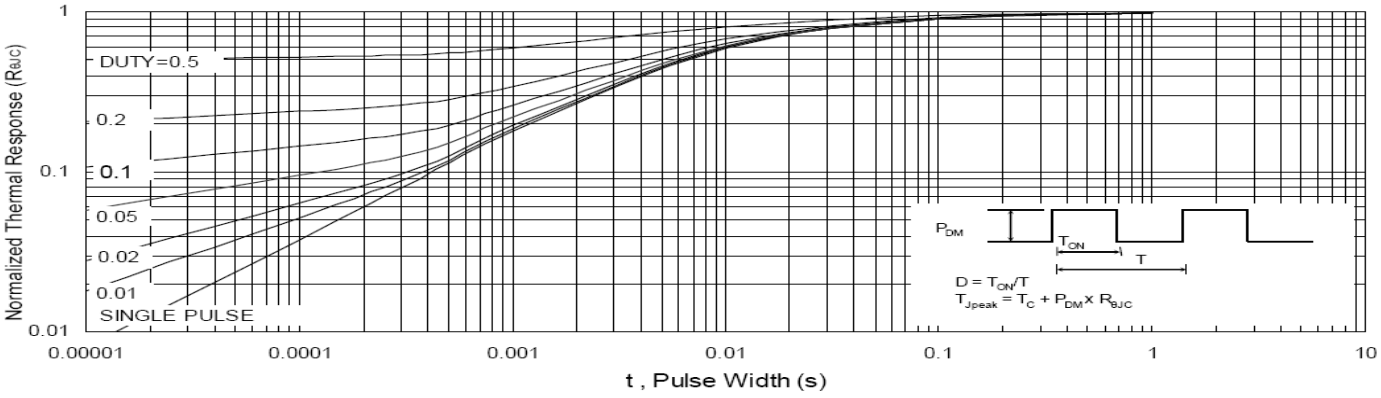

Fig. 9 Effective Transient Thermal Impedance

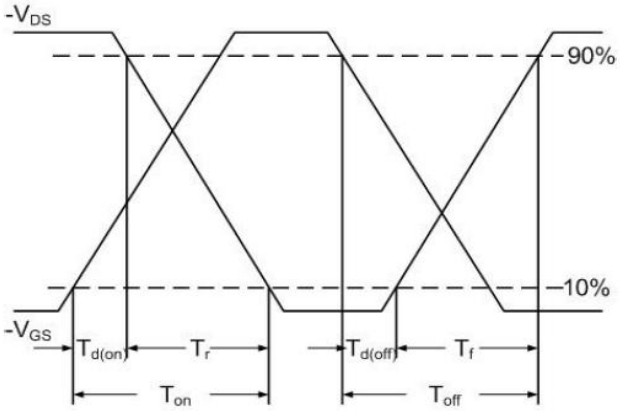

Fig. 10 Switching Time Waveform

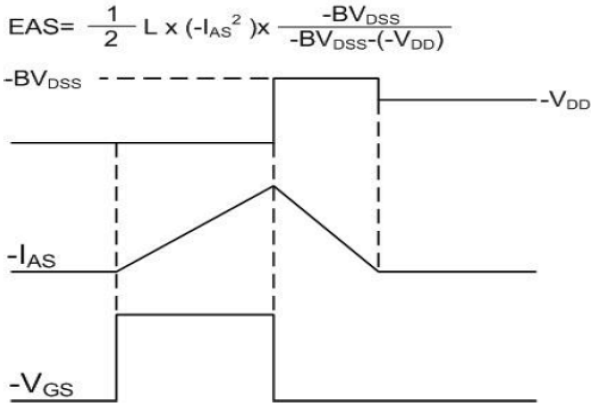

Fig. 11 Unclamped Inductive Waveform

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